

1-Line Bi-directional TVS Diode

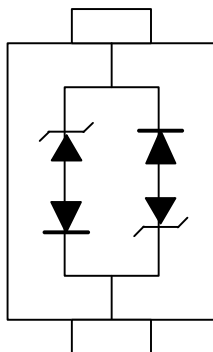
Description

The PESDR0561D3 is a 5V bi-direction TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The PESDR0561D3 has a low capacitance with a typical value at 0.6pF, and complies with the IEC 61000-4-2(ESD) standard with ±30kV air and ±30kV contact discharge. It is assembled into a lead-free SOD-323 package. The small size, low capacitance and high ESD surge protection make PESDR0561D3 an ideal choice to protect cellphone, wireless systems, and communication equipment.

Features

- 360W peak pulse power (8/20µs)
- Ultra low capacitance: 0.6pF typical
- Ultra low leakage: nA level
- Low operating voltage: 5 V
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: ±30kV
 - Contact discharge: ±30kV
 - IEC 61000-4-5 (Lightning) 18A (8/20µs)
- RoHS Compliant

Dimensions and Pin Configuration



Circuit and Pin Schematic

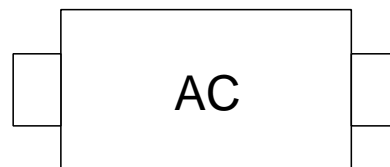
Mechanical Characteristics

- Package: SOD-323
- Case Material: “Green” Molding Compound.
- Moisture Sensitivity: Level 1 per J-STD-020
- Marking Information: See Below

Applications

- High-speed data lines
- Smart phones
- USB Ports
- Wireless Systems
- Ethernet10/100/1000 Base T

Marking Information



AC = Device Marking Code

Ordering Information

Part Number	Shipping	Reel Size
PESDR0561D3	3000/Tape &Reel	7 inch

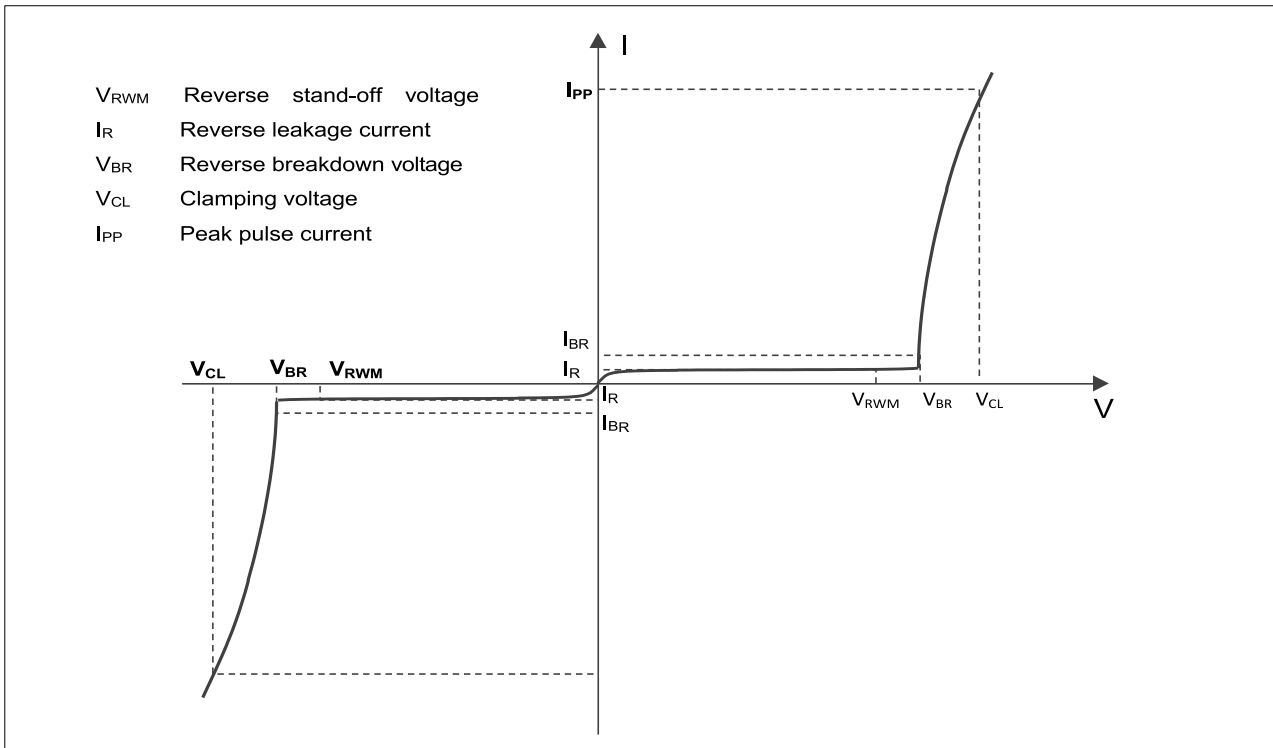
Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	P _{PK}	360	W
Peak Pulse Current (8/20μs)	I _{PP}	18	A
ESD per IEC 61000-4-2 (Air)	V _{ESD}	±30	kV
ESD per IEC 61000-4-2 (Contact)		±30	kV
Lead temperature	T _L	260	°C
Operating Temperature Range	T _{OP}	-40 ~ +85	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

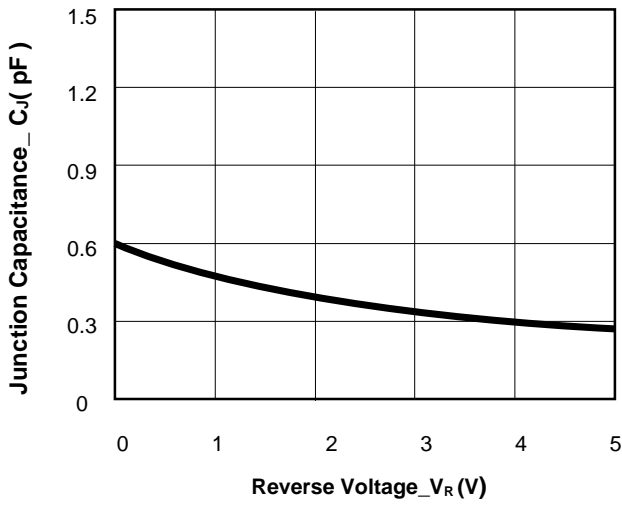
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			5	V	
Reverse Breakdown Voltage	V _{BR}	6.1	6.8	8	V	I _T = 1mA
Reverse Leakage Current	I _R			200	nA	V _{RWM} = 5 V
Clamping Voltage	V _C		8	10	V	I _{PP} = 1A (8/20μs pulse)
Clamping Voltage	V _C		16	20	V	I _{PP} = 18A (8/20μs pulse)
Junction Capacitance	C _J		0.6	0.9	pF	V _R = 0V, f = 1MHz

Electrical characteristics ($T_A = 25^\circ\text{C}$, unless otherwise noted)

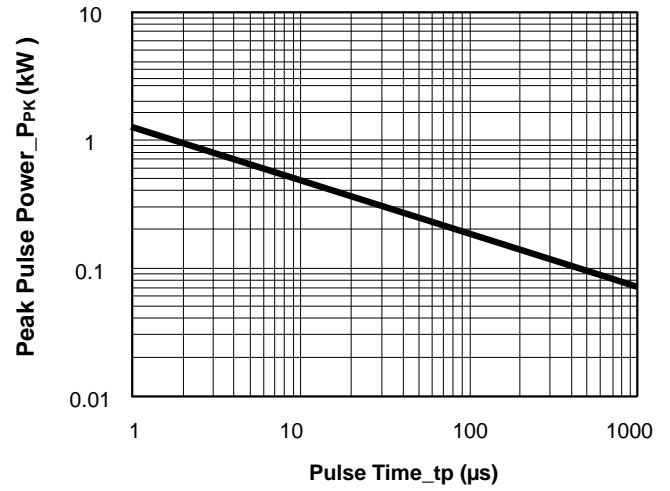


Definitions of electrical characteristics

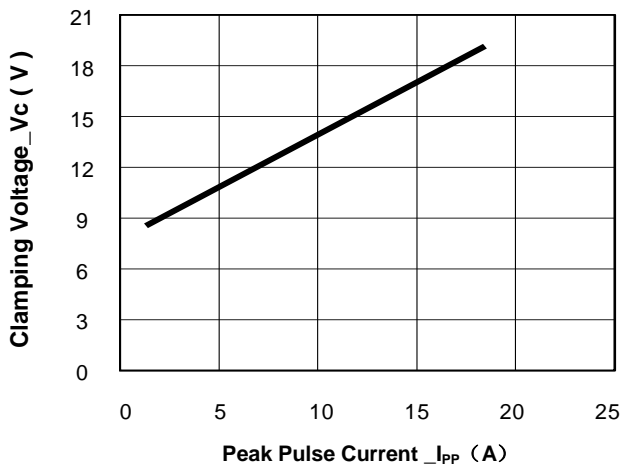
Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)



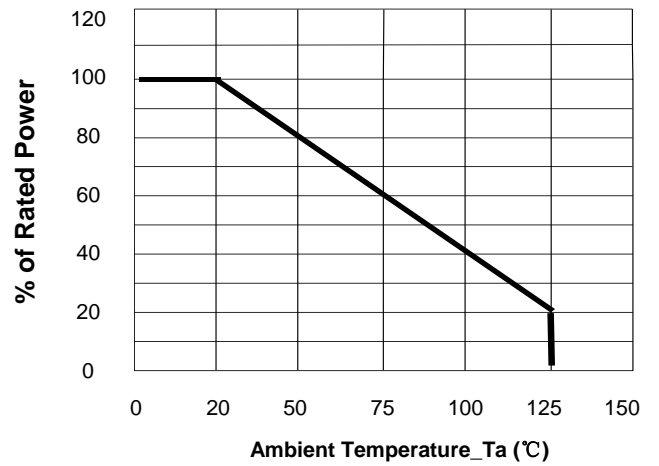
Junction Capacitance vs. Reverse Voltage



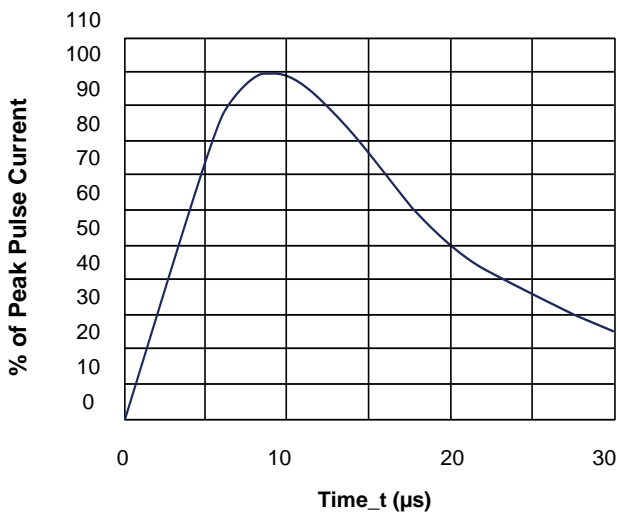
Peak Pulse Power vs. Pulse Time



Clamping Voltage vs. Peak Pulse Current

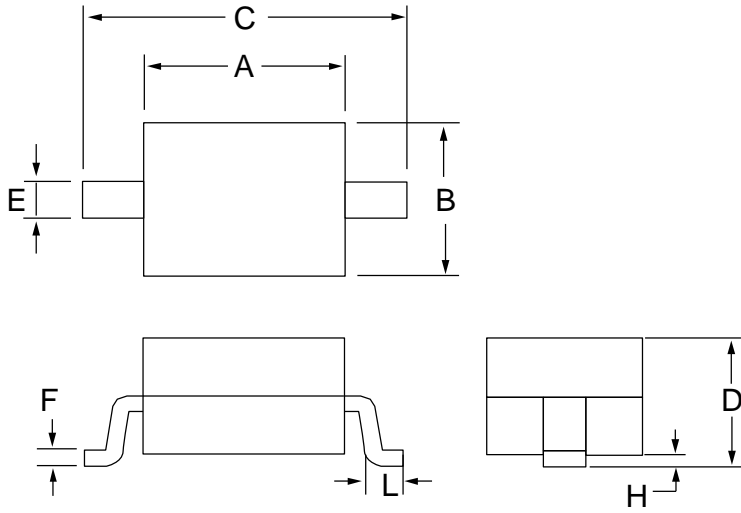


Power Derating Curve



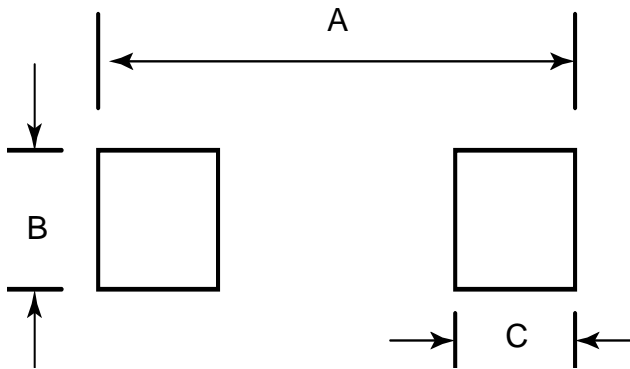
8/20 μs Pulse Waveform

SOD-323 Package Outline Drawing



SYM	DIMENSIONS				
	MILLIMETERS			INCHES	
	MIN	NOM	MAX	MIN	MAX
A	1.50	1.65	1.80	0.060	0.071
B	1.20	1.30	1.40	0.045	0.054
C	2.30	2.50	2.70	0.090	0.107
D	-		1.10	-	0.043
E	0.30		0.40	0.012	0.016
F	0.10		0.25	0.004	0.010
L	0.20		0.40	0.008	0.016
H	-		0.10	-	0.004

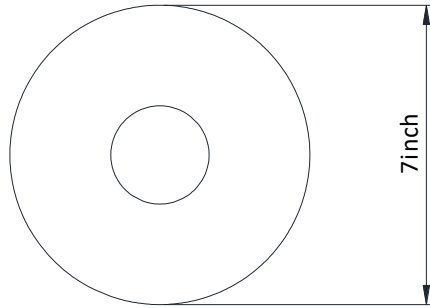
Suggested Land Pattern



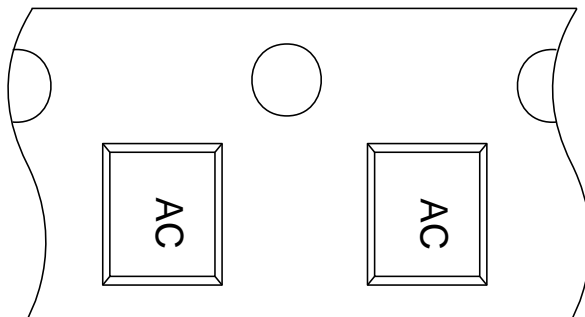
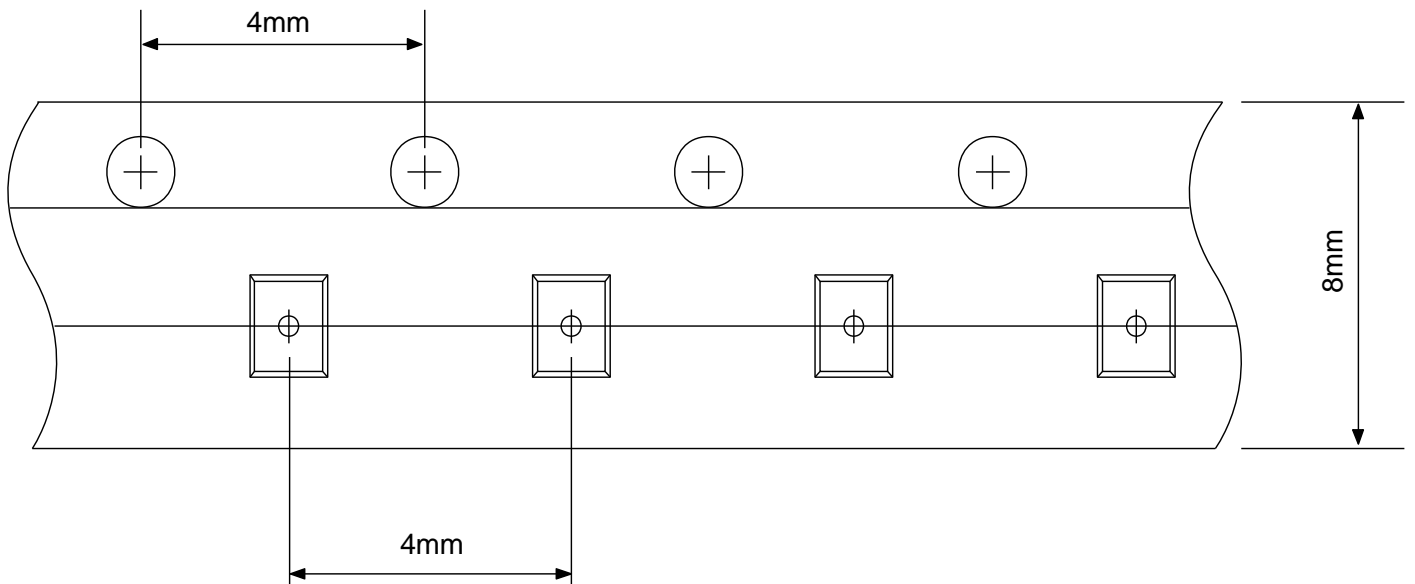
SYM	DIMENSIONS	
	MILLIMETERS	INCHES
A	3.15	0.120
B	0.80	0.031
C	0.80	0.031

TAPE AND REEL INFORMATION

Reel Dimensions



Tape Dimensions



User Direction of Feed

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